



**THE DATASHEET OF  
DMP6050SSD-13**



## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	$I_D$ $T_C = +25^\circ C$
-60V	55m $\Omega$ @ $V_{GS} = -10V$	-11.3A
	70m $\Omega$ @ $V_{GS} = -4.5V$	-9.1A

## Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

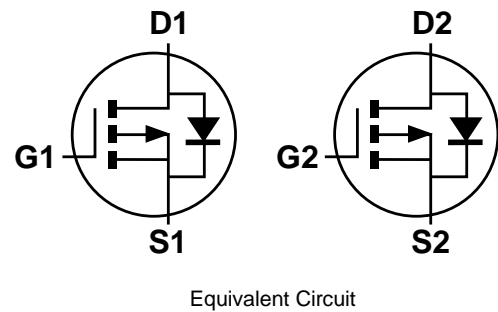
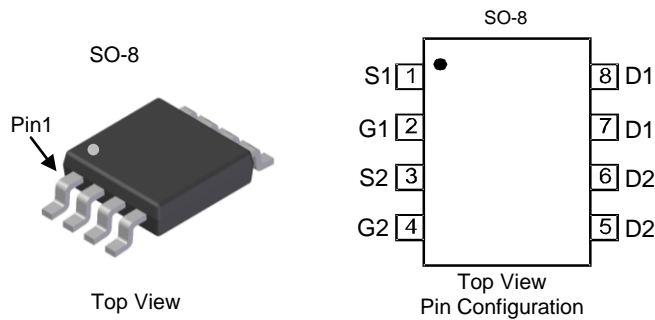
- DC-DC Converters
- Power Management Functions
- Backlighting

## Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

## Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208<sup>e3</sup>
- Weight: 0.076 grams (Approximate)

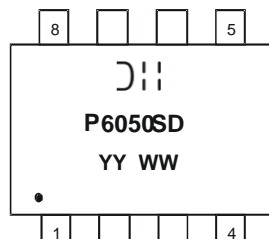


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP6050SSD-13	SO-8	2500 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



Dii = Manufacturer's Marking  
 P6050SD = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY or YY = Year (ex: 14 = 2014)  
 WW = Week (01 - 53)

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	-60	V	
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V	
Continuous Drain Current (Note 6) $V_{GS} = -10\text{V}$	$I_D$	$T_C = +25^\circ\text{C}$	-11.3	A
		$T_C = +70^\circ\text{C}$	-9.1	A
Pulsed Drain Current (10 $\mu\text{s}$ pulse, duty cycle = 1%)	$I_D$	$T_A = +25^\circ\text{C}$	-4.8	A
		$T_A = +70^\circ\text{C}$	-3.9	A
Maximum Continuous Body Diode Forward Current (Note 6)	$I_S$	-2.8	A	
Avalanche Current (Note 7) $L = 0.1\text{mH}$	$I_{AS}$	-24.8	A	
Avalanche Energy (Note 7) $L = 0.1\text{mH}$	$E_{AS}$	30.8	mJ	

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	$P_D$	$T_A = +25^\circ\text{C}$	1.2	W
		$T_A = +70^\circ\text{C}$	0.9	
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	Steady state	104	$^\circ\text{C/W}$
		$t < 10\text{s}$	45	
Total Power Dissipation (Note 6)	$P_D$	$T_A = +25^\circ\text{C}$	1.7	W
		$T_A = +70^\circ\text{C}$	1.1	
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	Steady state	72	$^\circ\text{C/W}$
		$t < 10\text{s}$	37	
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	13	$^\circ\text{C/W}$	
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$	

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-60	—	—	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	$I_{DSS}$	—	—	-1	$\mu\text{A}$	$V_{DS} = -60\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	—	-3.0	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	-	36	55	m $\Omega$	$V_{GS} = -10\text{V}, I_D = -5\text{A}$
		-	47	70		$V_{GS} = -4.5\text{V}, I_D = -4\text{A}$
Diode Forward Voltage	$V_{SD}$	-	-0.7	-1.2	V	$V_{GS} = 0\text{V}, I_S = -1\text{A}$
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	$C_{iss}$	-	1293	-	pF	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	-	86.3	-	pF	
Reverse Transfer Capacitance	$C_{rss}$	-	64.7	-	pF	
Gate Resistance	$R_g$	-	12	-	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ( $V_{GS} = -4.5\text{V}$ )	$Q_g$	-	11.9	-	nC	$V_{DS} = -30\text{V}, I_D = -5\text{A}$
Total Gate Charge ( $V_{GS} = -10\text{V}$ )	$Q_g$	-	24	-	nC	
Gate-Source Charge	$Q_{gs}$	-	3.6	-	nC	
Gate-Drain Charge	$Q_{gd}$	-	5.7	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	4.3	-	ns	
Turn-On Rise Time	$t_r$	-	6.3	-	ns	$V_{GS} = -10\text{V}, V_{DS} = -30\text{V}, R_G = 3\Omega, I_D = -5\text{A}$
Turn-Off Delay Time	$t_{D(off)}$	-	46.7	-	ns	
Turn-Off Fall Time	$t_f$	-	25.3	-	ns	
Body Diode Reverse Recovery Time	$t_{rr}$	—	13.6	—	ns	$I_F = -5\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	$Q_{rr}$	—	7.4	—	nC	$I_F = -5\text{A}, di/dt = 100\text{A}/\mu\text{s}$

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  - $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_J = +25^\circ\text{C}$ .
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

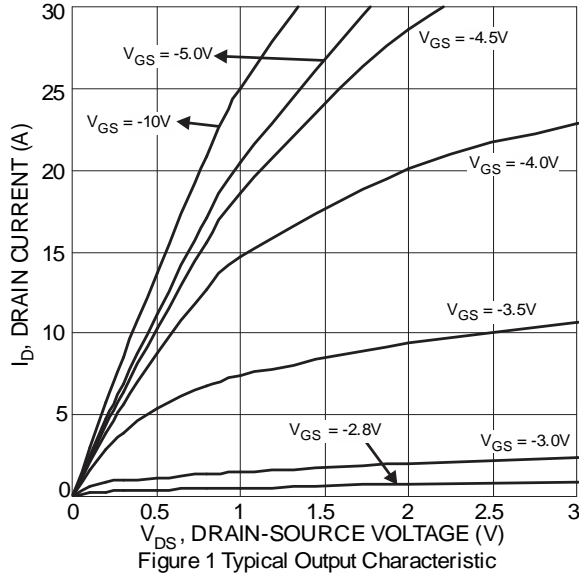


Figure 1 Typical Output Characteristic

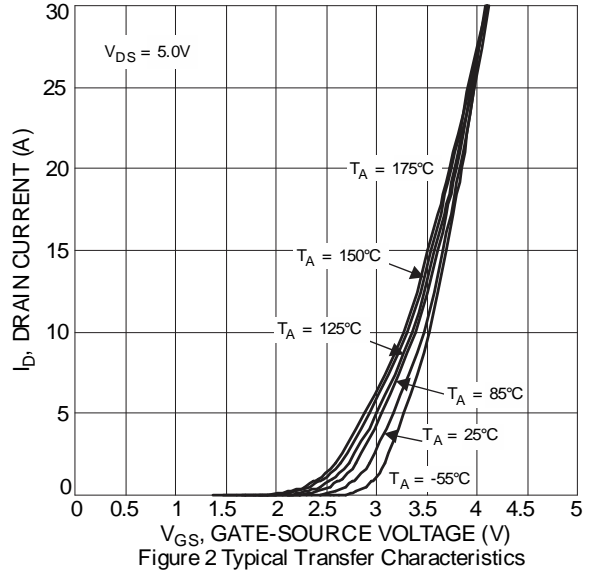


Figure 2 Typical Transfer Characteristics

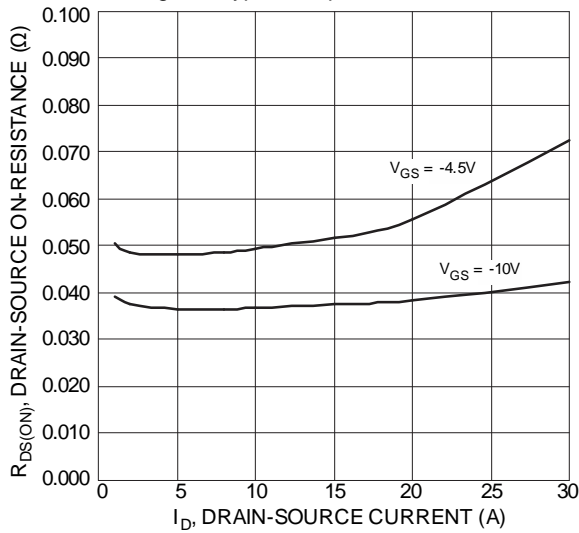


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

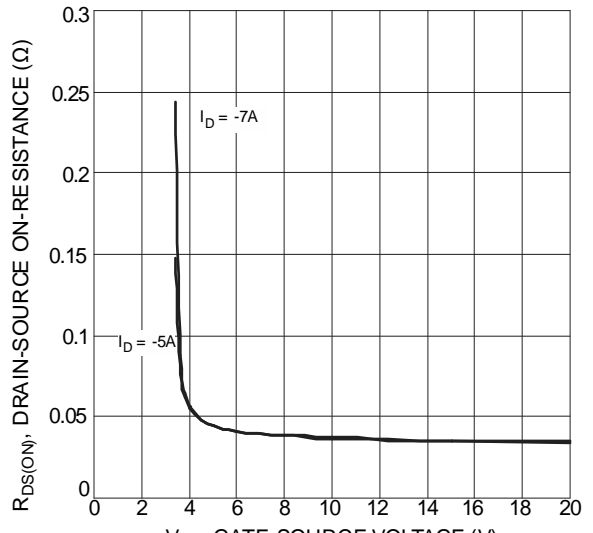


Figure 4 Typical Transfer Characteristics

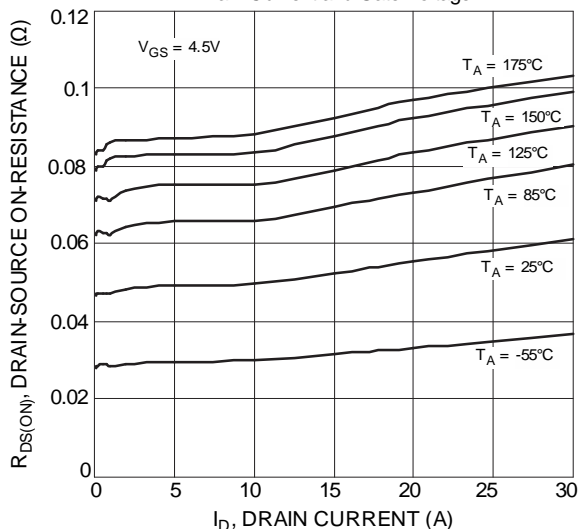


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

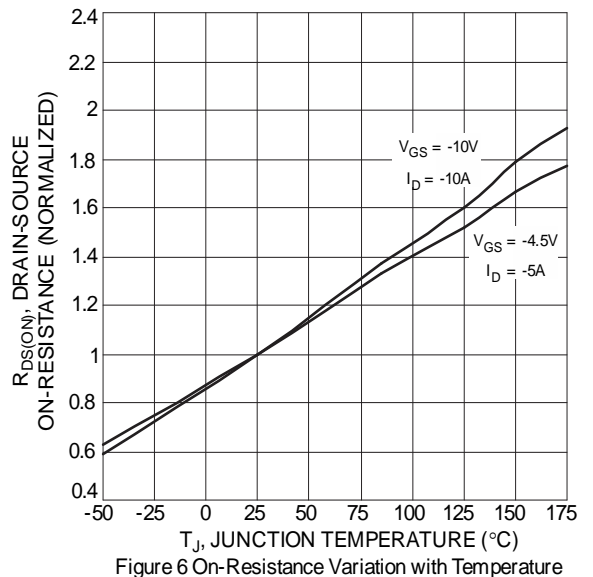


Figure 6 On-Resistance Variation with Temperature

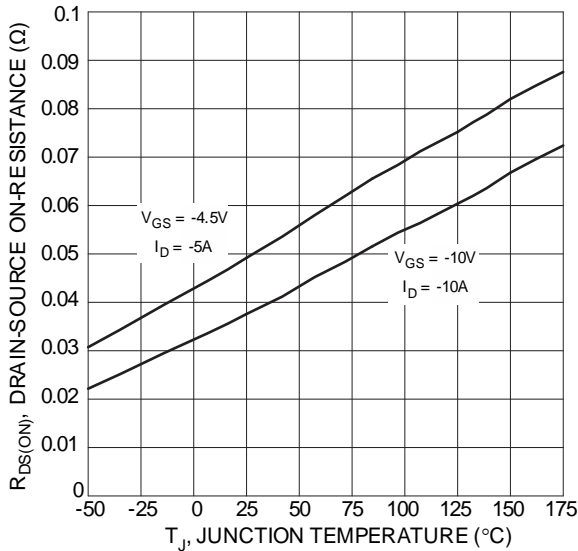


Figure 7 On-Resistance Variation with Temperature

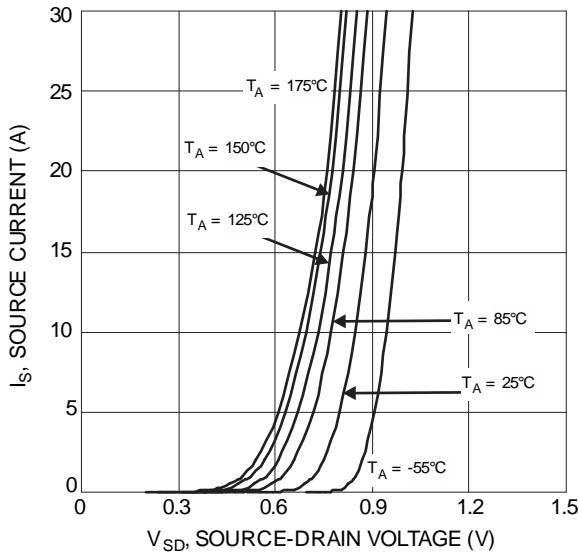


Figure 9 Diode Forward Voltage vs. Current

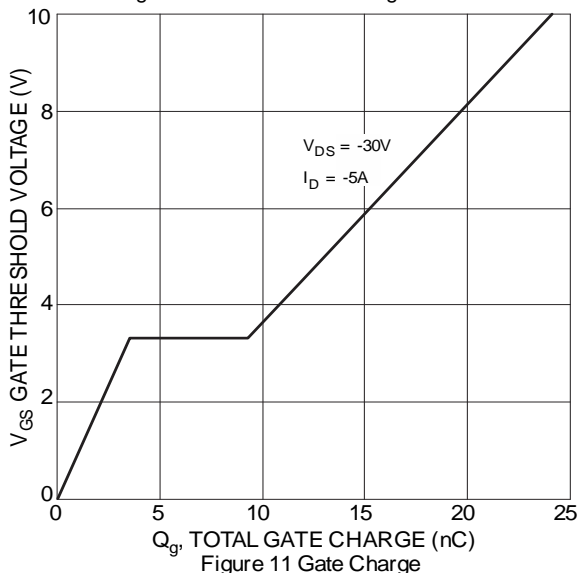


Figure 11 Gate Charge

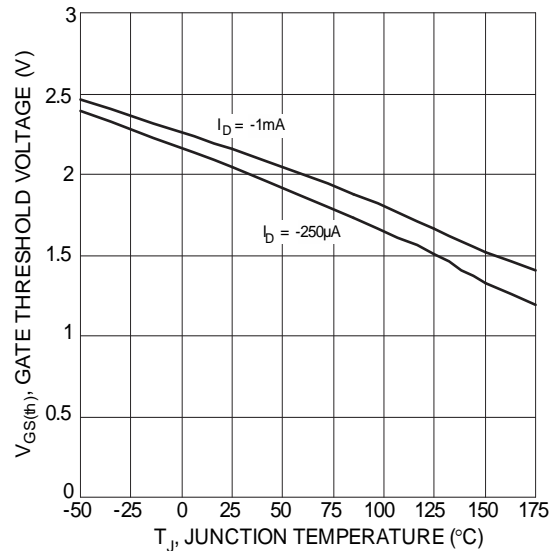


Figure 8 Gate Threshold Variation vs. Ambient Temperature

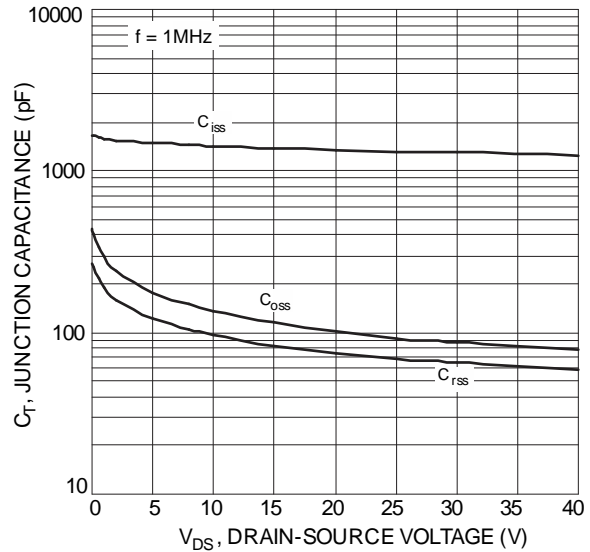


Figure 10 Typical Junction Capacitance

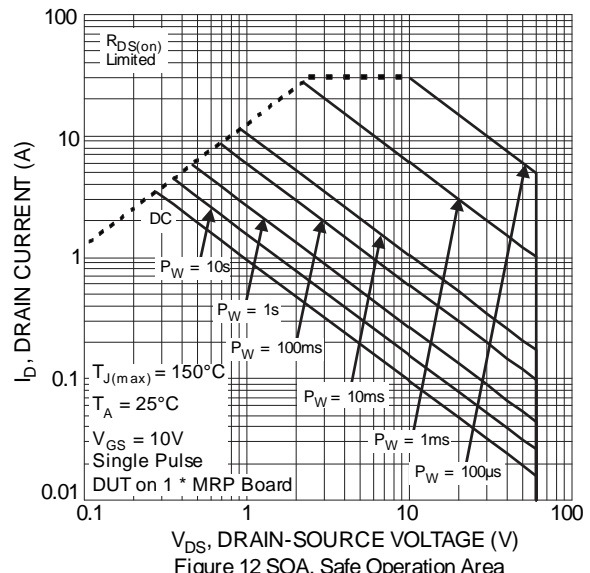


Figure 12 SOA, Safe Operation Area

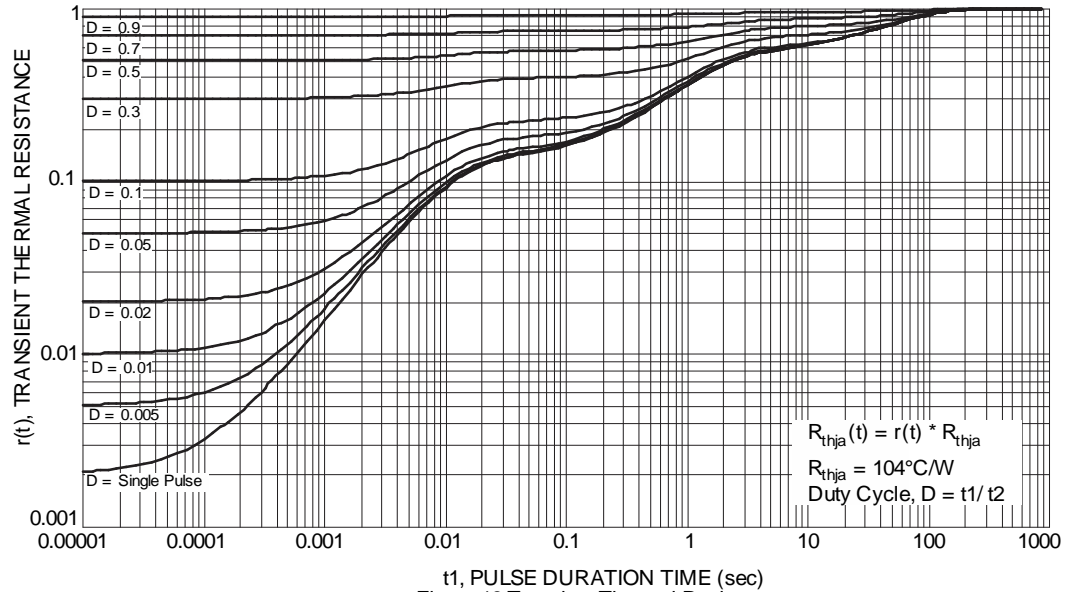
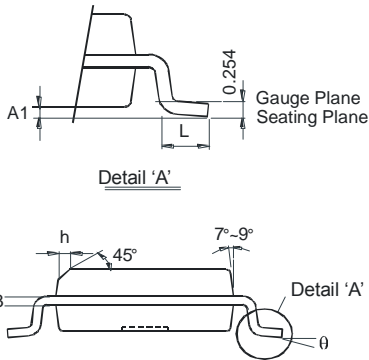
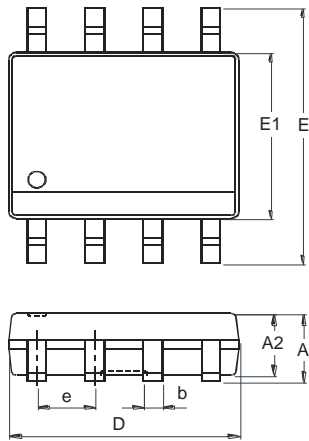


Figure 13 Transient Thermal Resistance

**Package Outline Dimensions**

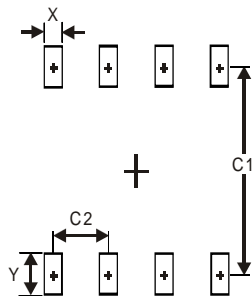
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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